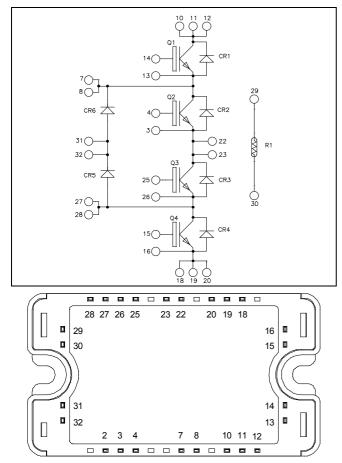


# APTGL60TL120T3G

# Three level inverter Trench + Field Stop IGBT4



All multiple inputs and outputs must be shorted together Example: 10/11/12 ; 7/8 ...

## Q1 to Q4 Absolute maximum ratings

## $V_{CES} = 1200V$ $I_{C} = 60A$ @ Tc = 80°C

### Application

- Solar converter
- Uninterruptible Power Supplies

#### Features

- Trench + Field Stop IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

#### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	80	
I <sub>C</sub>	Continuous Conector Current	$T_C = 80^{\circ}C$	60	А
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
$V_{GE}$	Gate – Emitter Voltage		±20	V
P <sub>D</sub>	Maximum Power Dissipation	$T_C = 25^{\circ}C$	280	W
RBSOA	Reverse Bias Safe Operating Area	$T_i = 150^{\circ}C$	100A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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## All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

## Q1 to Q4 Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				1	mA
V	Collector Emitter saturation Voltage			1.8	2.2	V	
V <sub>CE(sat)</sub>	Conector Ennitier saturation voltage		$T_{j} = 150^{\circ}C$		2.2		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 1.6 \text{mA}$		5.0	5.8	6.5	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE}$	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

## Q1 to Q4 Dynamic Characteristics

-	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			2770		
C <sub>oes</sub>	Output Capacitance				205		pF
C <sub>res</sub>	Reverse Transfer Capacitance				160		
Q <sub>G</sub>	Gate charge	$V_{GE} = \pm 15V$ ; $V_{CE} = 600V$ $I_{C} = 50A$			0.38		μC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switch	hing (25°C)		50		
T <sub>r</sub>	Rise Time	$V_{GE} = \pm 15V$			27		ns
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{CE} = 600V$ $I_{C} = 50A$			270		
T <sub>f</sub>	Fall Time	$R_G = 8.2\Omega$			70		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$			50		ns
Tr	Rise Time				30		
T <sub>d(off)</sub>	Turn-off Delay Time	$I_C = 50A$	-		290		
T <sub>f</sub>	Fall Time	$R_G = 8.2\Omega$			80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25^{\circ}C$		3.8		mJ
Lon	Tuni-on Switching Energy		$T_{\rm J} = 150^{\circ}{\rm C}$		5.5		1115
E <sub>off</sub>	Turn-off Switching Energy	$I_{\rm C} = 50 \text{A}$	$T_J = 25^{\circ}C$		2.5		mJ
LOII	Fun on Switching Energy	$R_G = 8.2\Omega$	$T_{\rm J} = 150^{\circ}{\rm C}$		4.5		1115
I <sub>sc</sub>	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = 900V$ $t_p \le 10\mu s$ ; $T_j = 150^{\circ}C$			200		А
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.53	°C/W



# APTGL60TL120T3G

### **CR1 to CR6 diode ratings and characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			1200			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =600V	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			100 500	μΑ
I <sub>F</sub>	DC Forward Current		$Tc = 80^{\circ}C$		30		А
		$I_F = 30A$			2.6	3.1	
$V_{\rm F}$	Diode Forward Voltage	$I_F = 60A$			3.2		V
		$I_F = 30A$	$T_{i} = 125^{\circ}C$		1.8		v
t	Reverse Recovery Time	1 20 4	$T_j = 25^{\circ}C$		300		ns
t <sub>rr</sub>			$T_{j} = 125^{\circ}C$		380		115
0	Reverse Recovery Charge	$v_R = 800v$ di/dt = 200A/µs	$T_j = 25^{\circ}C$		360		nC
Qrr	Reverse Recovery Charge		$T_{i} = 125^{\circ}C$		1700		nC
E <sub>rr</sub>	Reverse Recovery Energy	$I_F = 30A$ $V_R = 800V$ $di/dt = 1000A/\mu s$	$T_j = 125^{\circ}C$		1.6		mJ
$R_{thJC}$	Junction to Case Thermal Resistance					1.2	°C/W

## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B <sub>25/85</sub>	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		$T_C=100^{\circ}C$		4		%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

## Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range		-40		175		
T <sub>STG</sub>	Storage Temperature Range			-40		125	°C
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

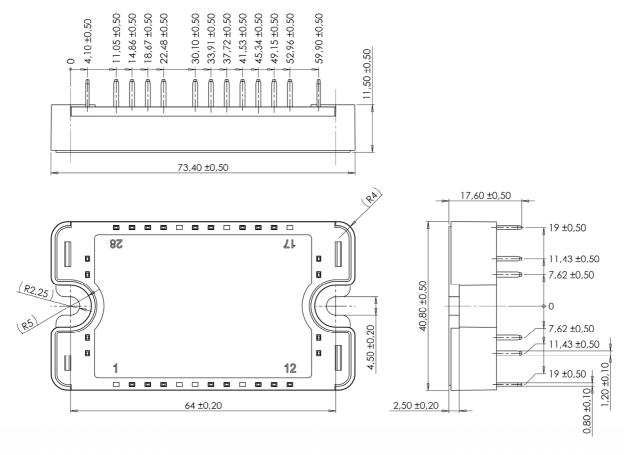
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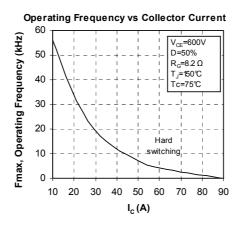


### SP3 Package outline (dimensions in mm)

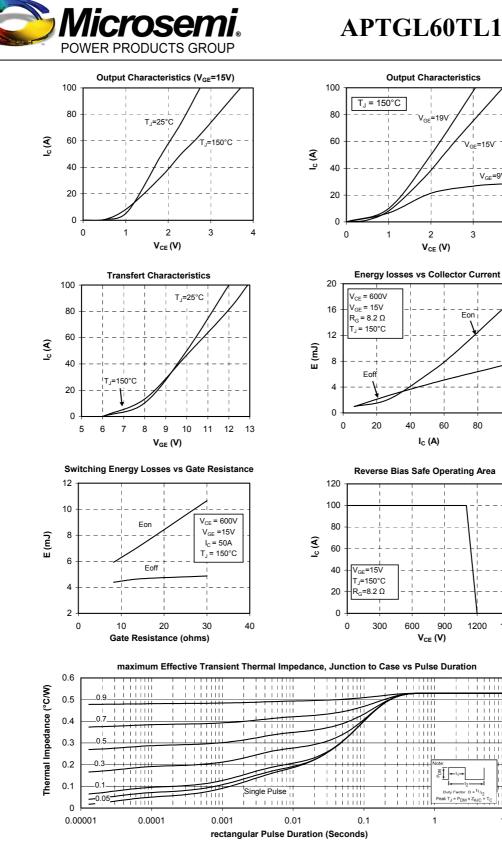


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

### Q1 to Q4 Typical performance curve



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=15V

3

V<sub>GE</sub>=9V

4

100

80

1200

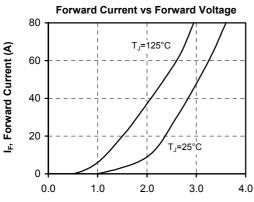
1500

10

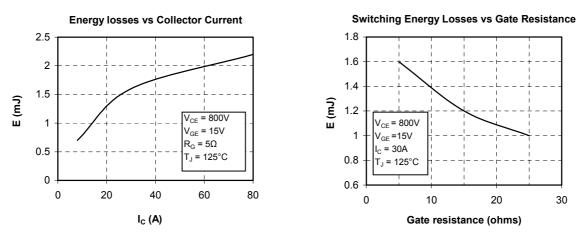




### CR1 to CR6 Typical performance curve



V<sub>F</sub>, Anode to Cathode Voltage (V)



Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration 1.4 1 1 1 1 1 1 1 1 1 1++++Thermal Impedance (°C/W) 1.2 0.9 1 1 1 1 TIT 1 1 1 1 1 <u>| | | | | |</u> 1 0.7 1111 0.8 0.5 1 1 1 1 1 1 1 1 1 0.6 0.3 1 1 1 1 Pow 0.4 0.1 \_Single Pulse 0.2 -Duty Factor D =  $t_{1/t_2}$ -0.05 Peak T<sub>J</sub> = P<sub>DM</sub> x  $Z_{\theta JC}$  + T<sub>C</sub> 0 0.00001 0.0001 0.001 0.01 0.1 10 1 **Rectangular Pulse Duration (Seconds)** 



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